# Anisotropic electronic structure of Ba(Fe<sub>0.96</sub>Ru<sub>0.04</sub>)<sub>2</sub>As<sub>2</sub> in the magnetostructurally ordered phase

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# 1 Introduction

BaFe<sub>2</sub>As<sub>2</sub>, a typical parent compound of iron arsenide superconductors, exhibits a magneto-structural transition, below which an antiferromagnetic-orthorhombic (AFO) phase is formed. The resistivity measurement on detwinned samples has shown that the resistivity along the shorter axis with ferromagnetic spin alignment (often denoted as b axis) is higher than that along longer axis with ferromagnetic spin alignment (a axis) [1]. The inplane electronic anisotropy that develops as temperature is lowered through the transition was also successfully revealed by optical spectroscopy [2] and angle-resolved photoemission spectroscopy (ARPES) [3].

The origin of the orthorhombic transition has been discussed from the perspectives of spin fluctuations or the orbital degree of freedom (an unequal occupation of  $d_{zx}$  / $d_{yz}$  orbitals) [4], which could result in the anisotropy of resistivity. In contrast, recent experimental results have given evidence that the resistivity anisotropy originates from an extrinsic scattering effect of impurity atoms [2,5]. In order to further understand the relationship between the anisotropy in the resistivity and that in the electronic structure, we have performed an ARPES measurement of detwinned Ba(Fe<sub>0.96</sub>Ru<sub>0.04</sub>)<sub>2</sub>As<sub>2</sub> crystals.

## 2 Experiment

High-quality single crystals of Ba(Fe<sub>0.96</sub>Ru<sub>0.04</sub>)<sub>2</sub>As<sub>2</sub> ( $T_s$ = 128 K) were grown using the self-flux method. In order to detwin samples in the AFO phase, we applied a uniaxial compressive stress along the tetragonal (110) direction using a mechanical device like that reported in ref. [6]. Angle-resolved photoemission (ARPES) experiments were carried out at BL 28A of Photon Factory (PF) using circularly-polarized light with the energy of 63eV. The crystals were cleaved *in situ* and measured at *T*= 20 K in an ultra-high vacuum of ~1x10<sup>-10</sup> Torr.

#### 3 Results and Discussion

Figure 1(b) shows the ARPES intensity map in the  $k_x$ - $k_y$  plane obtained with the integration window of 10meV about  $E_F$ . One can see the anisotropy of FSs with the broken four-fold symmetry. Band dispersions along the high symmetry lines Z-X and Z-Y are shown in Fig. 1(c)-(d). The band around the X point crosses the Fermi level while the one around the Y point sinks below  $E_F$ , which is consistent with the splitting of bands with  $d_{zx}$  and  $d_{yz}$  orbital character in the AFO phase of Ba(Fe<sub>1-x</sub>Co<sub>x</sub>)<sub>2</sub>As<sub>2</sub>



Fig. 1: Anisotropic electronic structure observed on detwinned Ba(Fe<sub>0.96</sub>Ru<sub>0.04</sub>)<sub>2</sub>As<sub>2</sub> single crystals in the AFO phase. (a) Schematic 2D BZ in the  $k_x$ - $k_y$  plane with  $k_z$ = $\pi$ , where Z-X is along the AFM axis and Z-Y is along the FM axis. (b) Fermi surface (FS) mapping in the  $k_x$ - $k_y$  plane using the photon energy of 63 eV ( $k_z$ = $\pi$ ). (c-d) Corresponding spectral images along the high symmetry lines showed in Fig.1(b).

reported by Yi *et al.* [3]. As proposed in ref. [5], resistivity anisotropy in the underdoped Ba $(Fe_{1-x}Co_x)_2As_2$  is induced by the doped atoms anisotropically polarizing its surroundings and working as anisotropic scattering centers in the AFO phase while the origin of the different sign of the in-plane resistivity along the different axes may root in the anisotropic electronic structure of the AFO phase. Recently, the opposite in-plane resistivity anisotropy in FeTe was reported [7], which implies that some anisotropic features of the electronic structure may be 90 ° rotated relative to the defined a/b axis in iron telluride.

### References

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